NSN 5961-01-203-5813

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Thyristor Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-203-5813 **Inclosure Material:** Metal **Overall Length:** 0.605 inches **Overall Diameter:** 1.900 inches **Mounting Method:** Press fit **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 2.4 on-state voltage, peak and 1200.0 repetitive peak off-state voltage and 1200.0 repetitive peak reverse voltage and 1400.0 nonrepetitive peak reverse voltage and 20.0 peak gate voltage **Current Rating Per Characteristic:** 225.00 amperes forward current, total rms horsepower metric and 1600.00 amperes peak forward surge current absolute **Power Rating Per Characteristic:** 2.0 watts small-signal input power, common-collector universal **Maximum Operating Tempurature Per Measurement Point:** 125.0 degrees celsius junction **Test Data Document:** 21877-167626 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc.; excludes any specification, standard or other document that may be referenced in a basic governing drawing) **Terminal Type And Quantity:** 1 insulated wire lead w/terminal lug and 2 case Shelf Life: N/a **Unit Of Measure:** Demilitarization: No Fiig: